

30V P-CHANNEL Enhancement Mode MOSFET

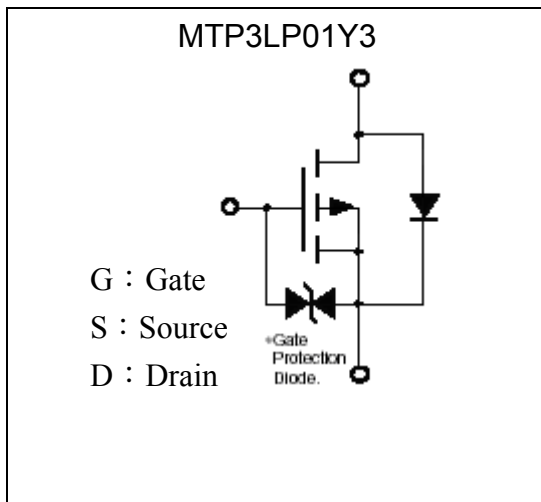
MTP3LP01Y3

BV _{DSS}	-30V
I _D	-230mA
R _{DS(on)(typ)}	3 Ω @-4V
	4.6 Ω @-2.5V
	10.9 Ω @-1.5V

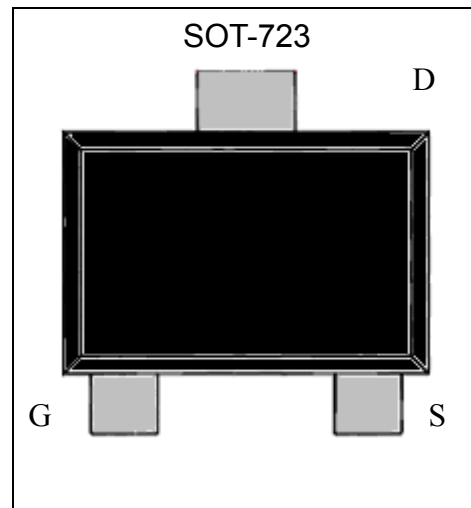
Features

- Ultra high speed switching.
- Low gate charge.
- 2.5V drive.
- ESD protected gate
- Pb-free package lead plating and halogen-free package.

Equivalent Circuit

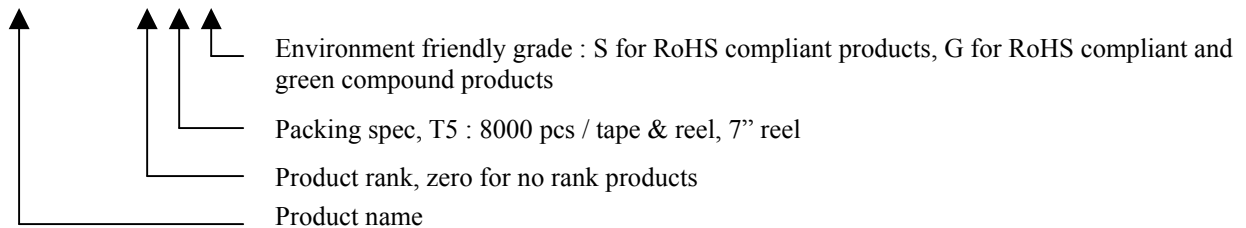


Outline



Ordering Information

Device	Package	Shipping
MTP3LP01Y3-0-T5-G	SOT-723 (Pb-free lead plating and halogen-free package)	8000 pcs / tape & reel





Absolute Maximum Ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	±10	
Continuous Drain Current	I _D	-230	mA
Pulsed Drain Current (Note 1)	I _{DM}	-920	
Maximum Power Dissipation (Note 2)	P _D	150	mW
Thermal Resistance, Junction-to-Ambient	R _{th,ja}	833	°C/W
Operating Junction and Storage Temperature	T _j , T _{stg}	-55~+150	°C

Note : 1. Pulse width ≤ 10μs, duty cycle ≤ 1%.
 2. When mounted on a glass epoxy with a dimension of 100mm² × 1mm.

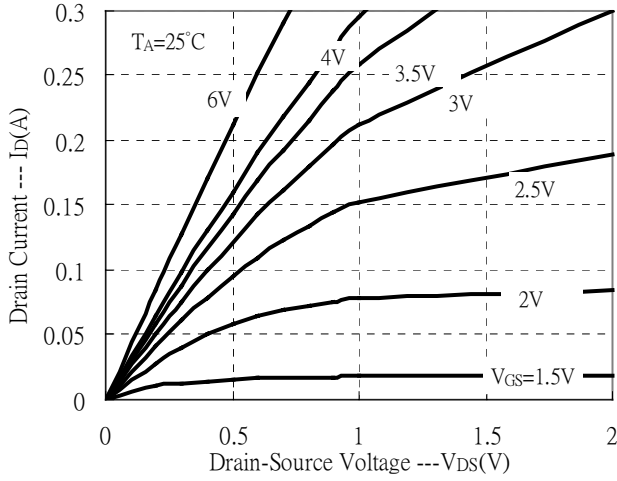
Electrical Characteristics (Ta=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-30	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-0.6	0.9	-1.1		V _{DS} =-10V, I _D =-100μA
G _{FS}	100	210	-	mS	V _{DS} =-10V, I _D =-100mA
I _{GSS}	-	-	±1	μA	V _{GS} =±8V, V _{DS} =0V
I _{DSS}	-	-	-1		V _{DS} =-30V, V _{GS} =0V
	-	-	-10		V _{DS} =-24V, V _{GS} =0V, T _j =125°C
*R _{DS(ON)}	-	3	5	Ω	V _{GS} =-4V, I _D =-100mA
	-	4.6	8		V _{GS} =-2.5V, I _D =-30mA
	-	10.9	18		V _{GS} =-1.5V, I _D =-1mA
Dynamic					
C _{iss}	-	35.7	-	pF	V _{DS} =-20V, V _{GS} =0V, f=1MHz
C _{oss}	-	11.9	-		
C _{rss}	-	3.7	-		
*t _{d(ON)}	-	26.4	-	ns	V _{DS} =-15V, I _D =-100mA, V _{GS} =-4V, R _L =150Ω, R _G =50Ω
*t _r	-	12.8	-		
*t _{d(OFF)}	-	31.5	-		
*t _f	-	46.4	-		
*Q _g	-	0.78	-	nC	V _{DS} =-10V, I _D =-100mA, V _{GS} =-10V
*Q _{gs}	-	0.1	-		
*Q _{gd}	-	0.1	-		
Source-Drain Diode					
*I _S	-	-	-230	mA	
*I _{SM}	-	-	-920		
*V _{SD}	-	0.83	-1.2	V	V _{GS} =0V, I _S =-100mA

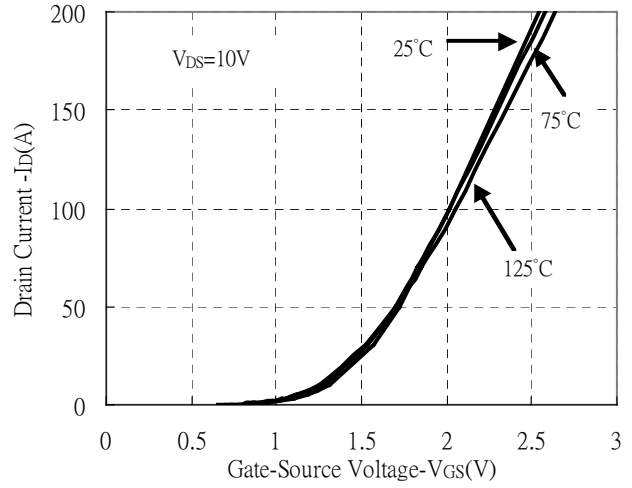
*Pulse Test : Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Typical Characteristics(The minus sign in voltage and current is omitted)

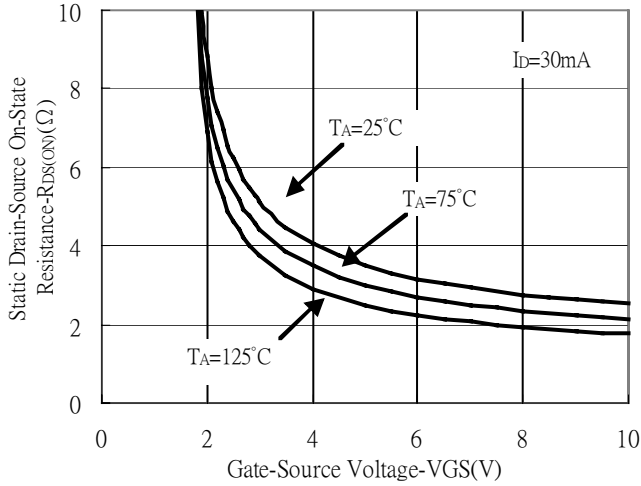
Typical Output Characteristics



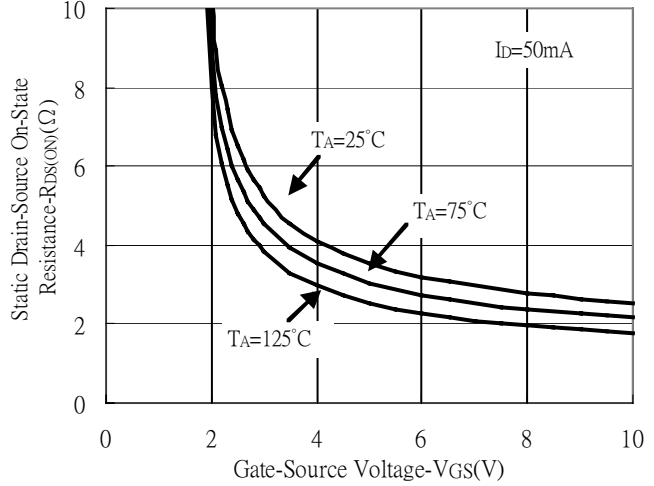
Typical Transfer Characteristics



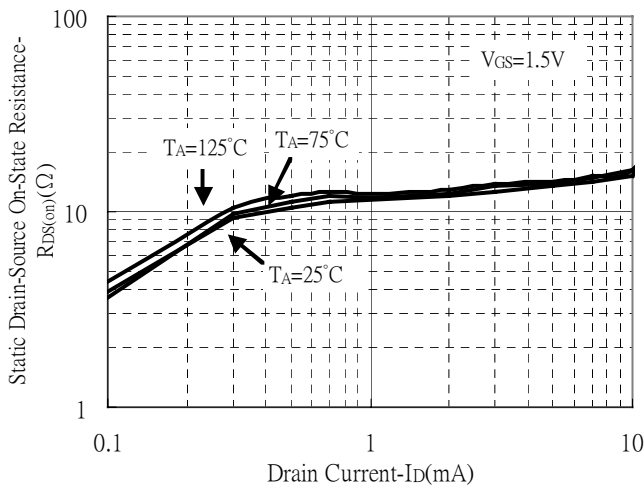
Static Drain-Source On-State Resistance vs Gate-Source Voltage



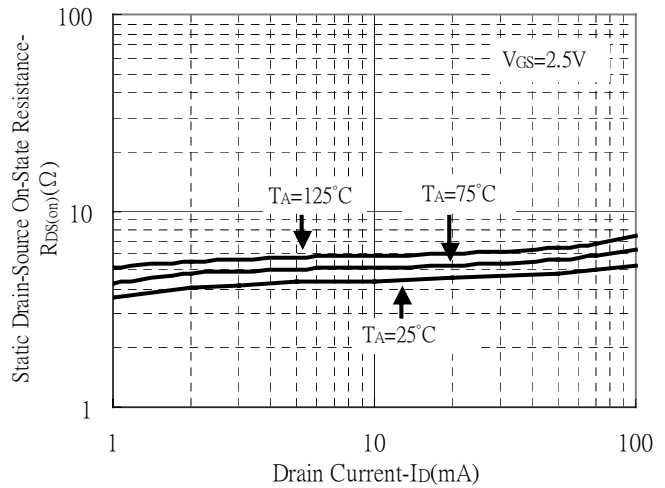
Static Drain-Source On-State Resistance vs Gate-Source Voltage



Static Drain-Source On-State resistance vs Drain Current

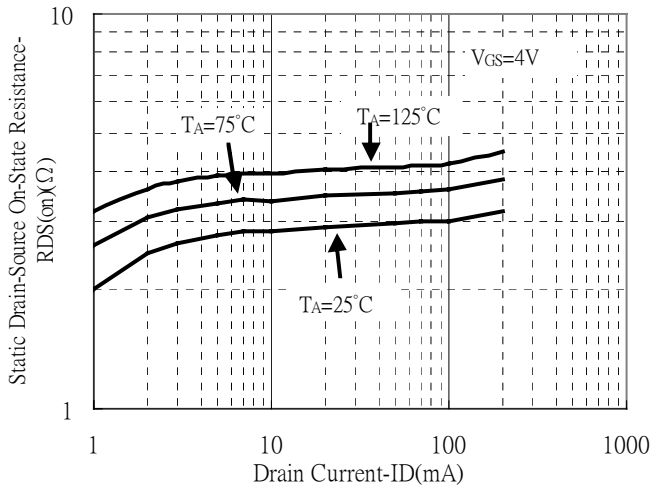


Static Drain-Source On-State resistance vs Drain Current

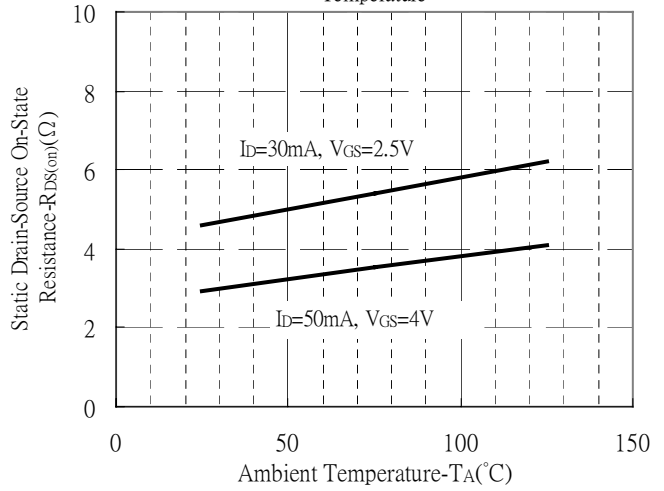


Typical Characteristics(Cont.)

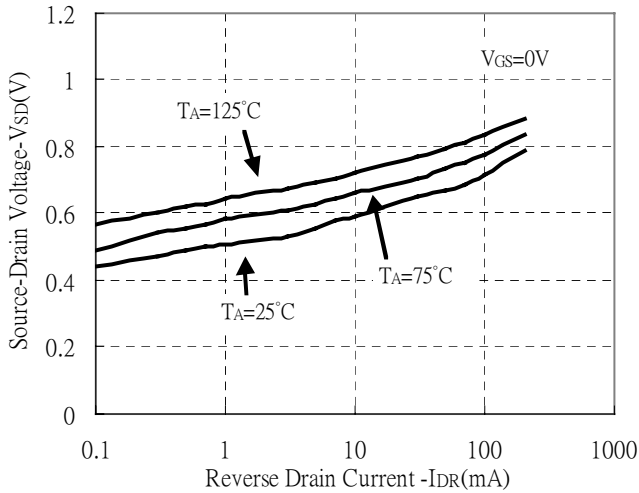
Static Drain-Source On-State resistance vs Drain Current



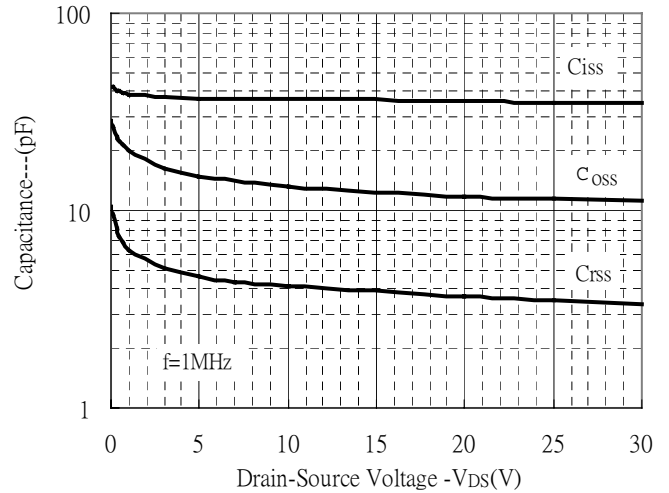
Static Drain-Source On-State resistance vs Ambient Temperature



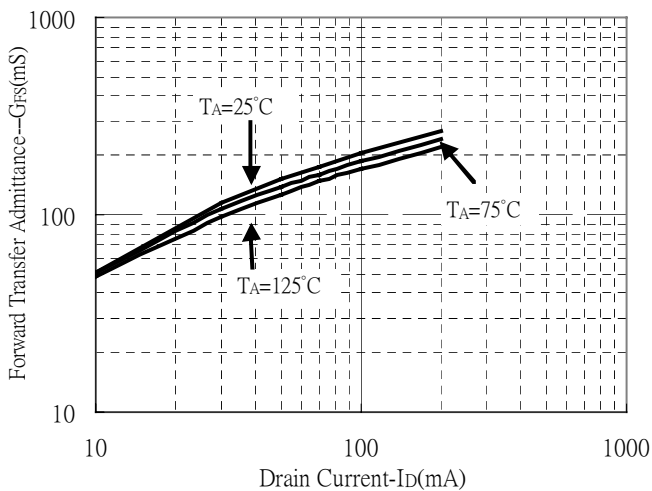
Reverse Drain Current vs Source-Drain Voltage



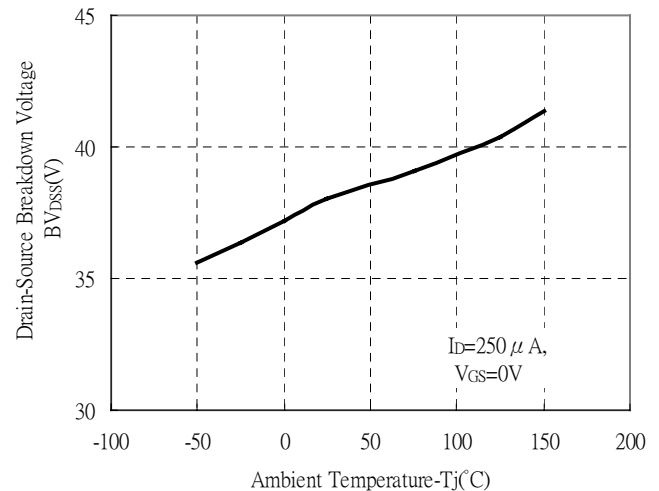
Capacitance vs Drain-to-Source Voltage



Forward Transfer Admittance vs Drain Current

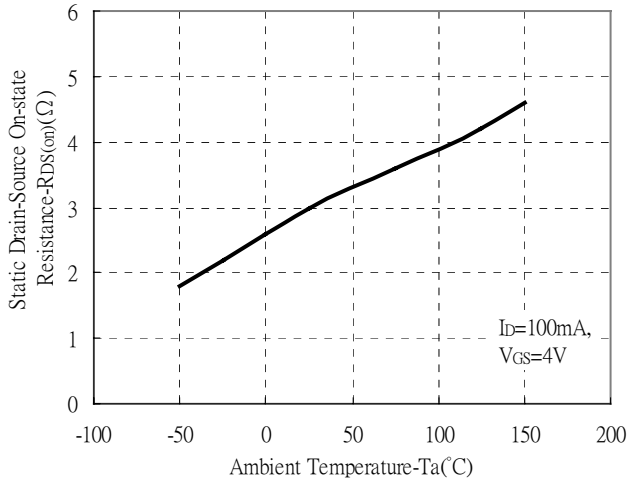


Breakdown Voltage vs Ambient Temperature

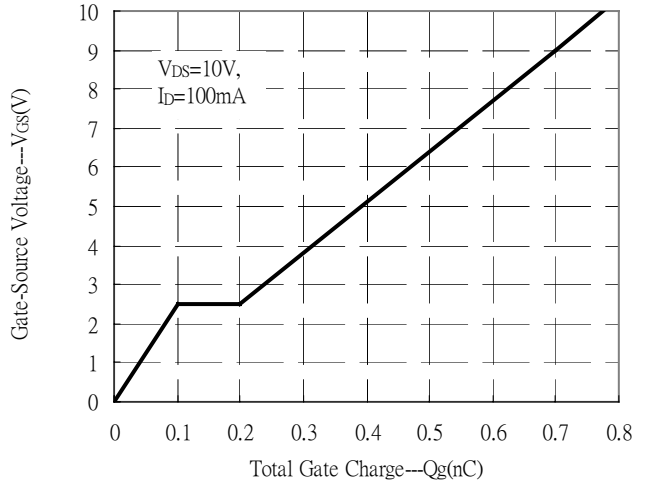


Typical Characteristics(Cont.)

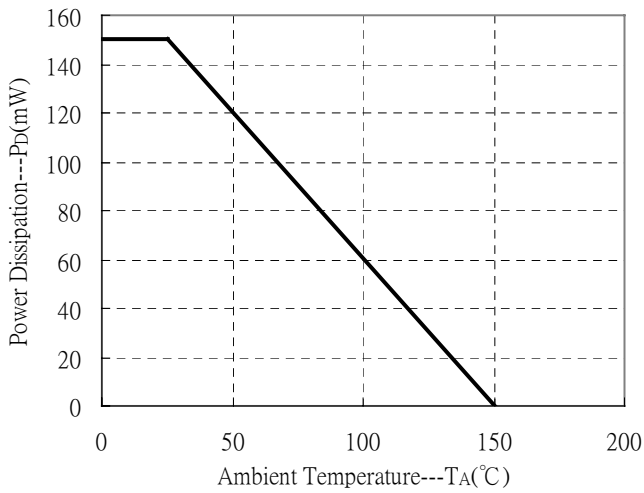
Static Drain-Source On-resistance vs Ambient Temperature



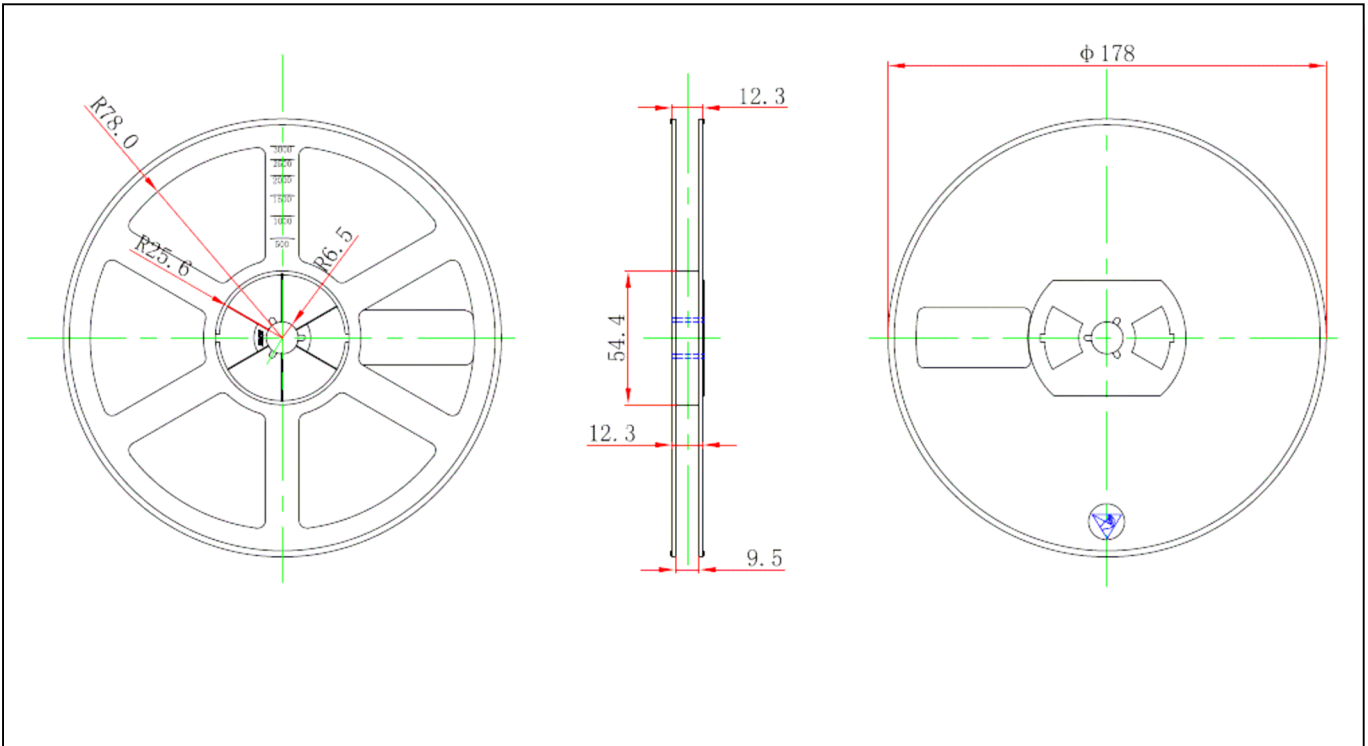
Gate Charge Characteristics



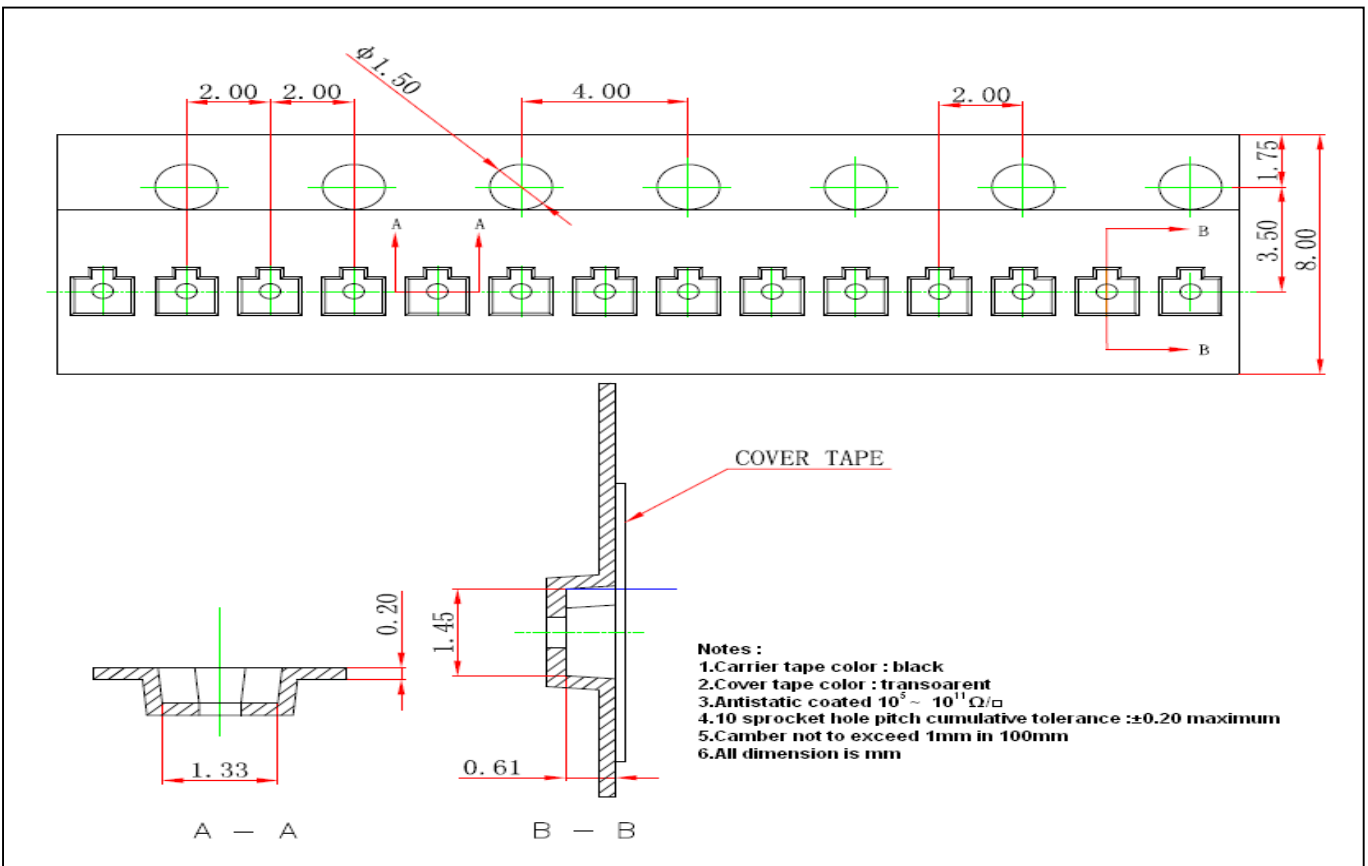
Power Derating Curve



Reel Dimension



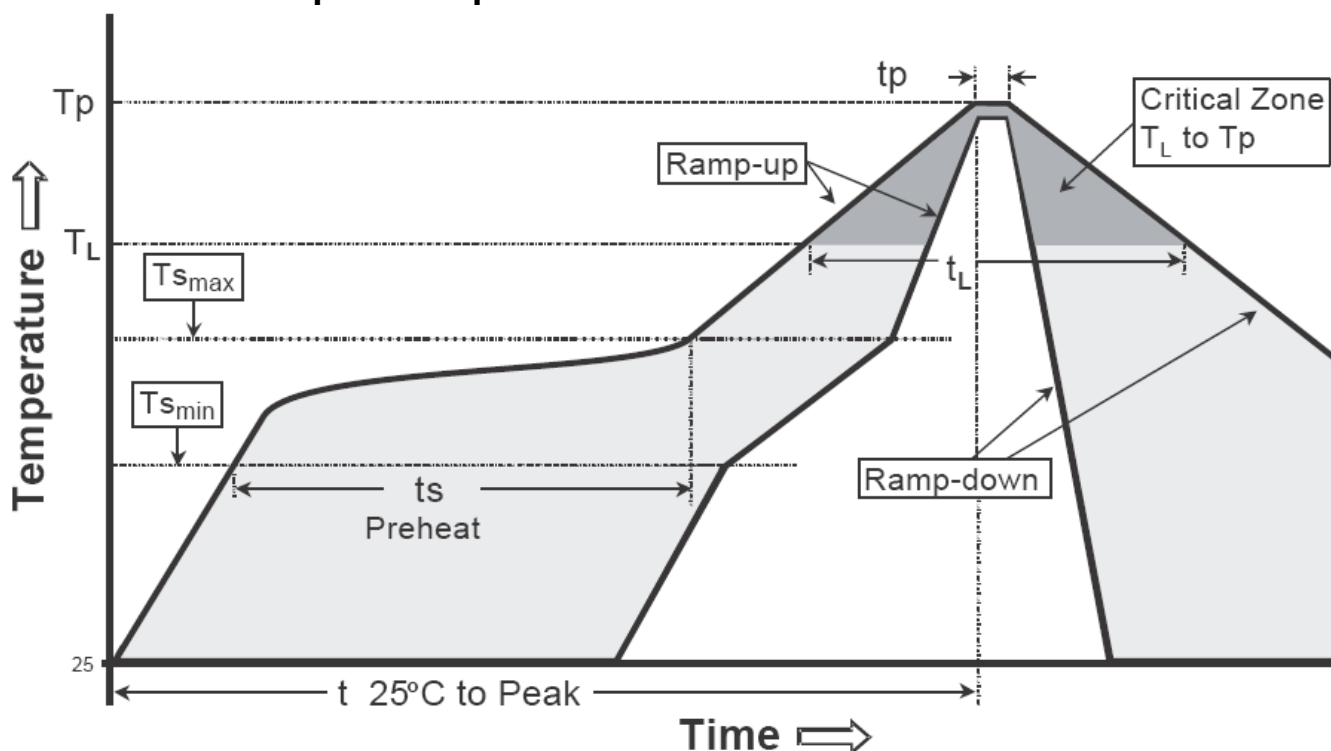
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

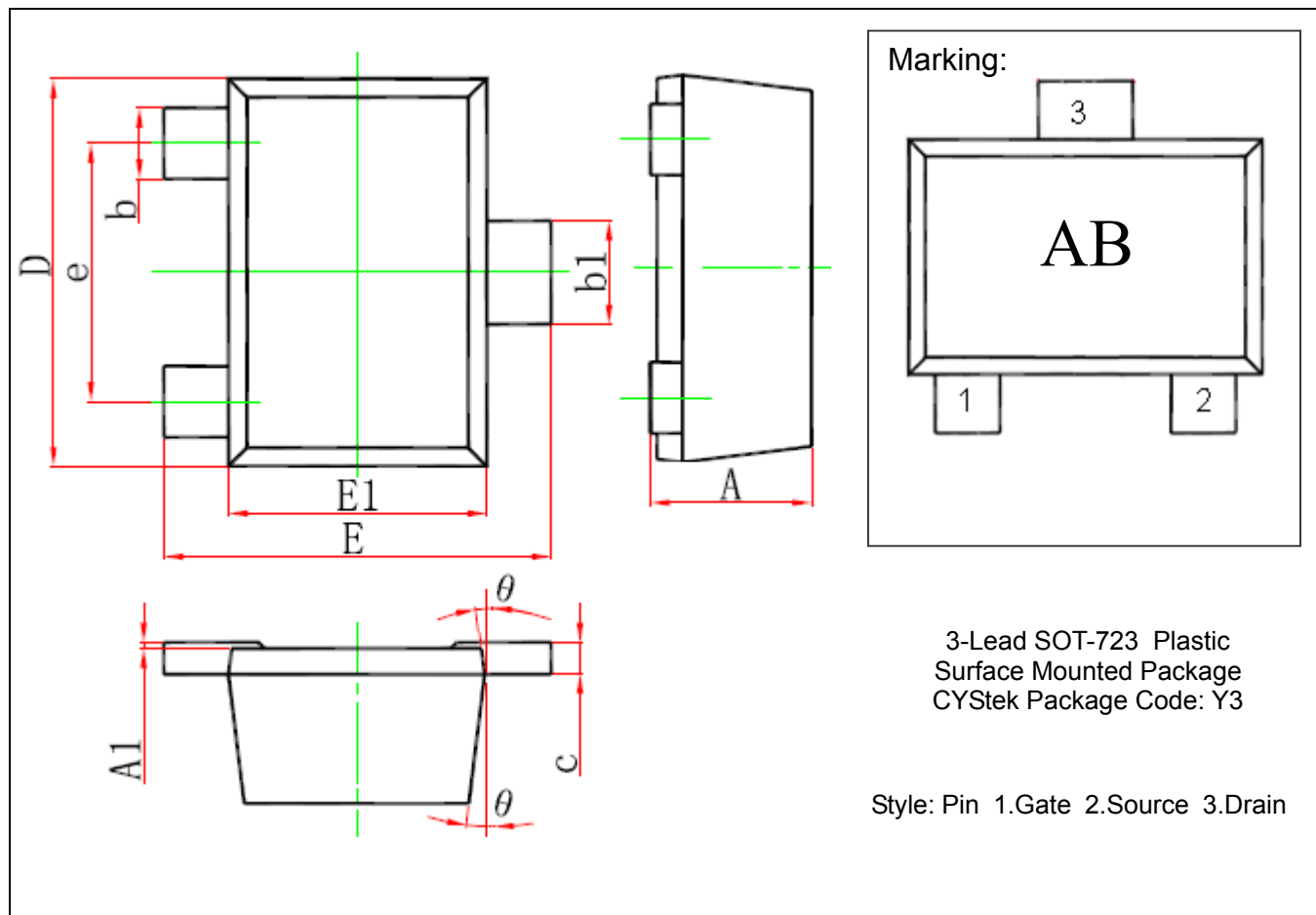
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

SOT-723 Dimension



*Typical

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.000	0.500	0.000	0.020	D	1.150	1.250	0.045	0.049
A1	0.000	0.050	0.000	0.002	E	1.150	1.250	0.045	0.049
b	0.170	0.270	0.007	0.011	E1	0.750	0.850	0.030	0.033
b1	0.270	0.370	0.011	0.015	e	0.800*		0.031*	
c	0.000	0.150	0.000	0.006	θ	7° REF		7° REF	

- Notes:**
- 1.Controlling dimension: millimeters.
 - 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 - 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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